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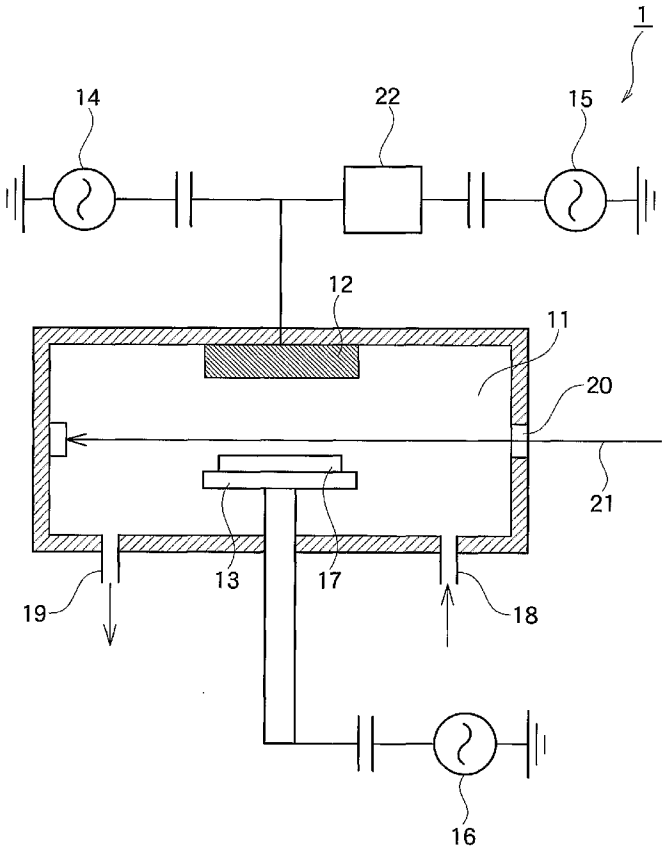
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(54) Title: RADICAL GENERATING METHOD, ETCHING METHOD AND APPARATUS FOR USE IN THESE METHODS



(57) Abstract: The method for generating radicals comprises: feeding F2 gas or a mixed gas of F2 gas and an inert gas into a chamber of which the inside is provided with a carbon material, supplying a carbon atom from the carbon material by applying a target bias voltage to the carbon material, and thereby generating high density radicals, wherein the ratio of CF3 radical, CF2 radical and CF radical is arbitrarily regulated by controlling the target bias voltage applied to the carbon material while measuring the infrared absorption spectrum of radicals generated inside the chamber.

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